

oxides, alloys thereof, and combinations thereof, wherein the first electrode extends above an uppermost surface of a substrate assembly;

forming a dielectric on the first electrode and the uppermost surface of the substrate assembly; and

forming a second electrode on the dielectric and the uppermost surface of the substrate assembly.

51. (Three Times Amended) The method of claim 38, wherein forming the first electrode includes:

forming a layer of hemispherical grain polysilicon on the substrate assembly; and
forming the first electrode on the hemispherical grain polysilicon.

52. (Twice Amended) A method of forming a capacitor, comprising:

forming a layer of hemispherical grain polysilicon;

forming a first electrode on the hemispherical grain polysilicon, wherein the first electrode is selected from a group consisting of transition metals, conductive metal-oxides, alloys thereof, and combinations thereof, and wherein the first electrode extends above an uppermost surface of a substrate assembly;

forming a dielectric on the first electrode and the uppermost surface of the substrate assembly; and

forming a second electrode on the dielectric and the uppermost surface of the substrate assembly.

Sub E1

D-1

58. (Twice Amended) A method, comprising:

forming a substrate assembly;

forming a layer of hemispherical grain polysilicon on the substrate assembly;

forming a first electrode on the hemispherical grain polysilicon, wherein the first electrode is selected from a group consisting of transition metals, conductive metal-oxides, alloys thereof, and combinations thereof, and wherein the first electrode extends above an uppermost surface of the substrate assembly;

removing a portion of the substrate assembly;

removing the hemispherical grain polysilicon;

forming a dielectric on the first electrode and the uppermost surface of the substrate assembly;

and

forming a second electrode on the dielectric and the uppermost surface of the substrate assembly.

REMARKS

This Amendment is a submission under 37 C.F.R. §1.114 for a Request for Continued Examination (RCE).

In the Office Action, claims 38-43, 45-49 and 51-60 were rejected. In addition, claim 51 was objected to for having a typographical error. By this amendment, claims 38, 51-52 and 58 have been amended. Thus, claims 38-43, 45-49 and 51-60 remain pending. For the reasons set forth hereinbelow, Applicants request that the objections and rejections associated with the pending